# **1** General description

The NX30P0121UK is an advanced 3A unidirectional power switch. It includes Undervoltage Lockout (UVLO), Overvoltage Lockout (OVLO) in VOUT, OVLO adjustable pin and over-temperature protection circuits. It is designed to automatically isolate the power switch terminals when a fault condition occurs. Both VIN and VOUT pins have 29V tolerance in shutdown mode.

The device has a default internal 14.5V overvoltage protection threshold in VOUT and adjustable OVP threshold by resistor divider from VOUT. ISNS pin is current source output proportional to input current from VIN to VOUT when device is enabled.

The device is enabled by external EN pin. When EN pin is driven LOW, the device is in shutdown mode where all internal circuitries are off and OVP switch is off. When EN pin is driven HIGH and VIN is valid, the OVP switch soft starts after VIN debounce time to limit the inrush current.

NX30P0121UK is offered in a small 12 bumps, 1.65 x 1.25 x 0.525 mm WLCSP package.

## 2 Features and benefits

- Wide supply voltage range from 2.5V to 20V
- Switch maximum 3A continuous current
- 29V tolerance on both VIN and VOUT pin
- 54mΩ (typical) Low ON resistance
- Adjustable overvoltage protection threshold, internal 14.5V VOUT OVLO
- Built in slew rate control for inrush current limit
- · ISNS to monitor input current from VIN to VOUT
- Protection circuitry
  - Over-temperature protection
  - Overvoltage protection
  - Undervoltage lockout
- ESD protection
  - HBM ANSI/ESDA/JEDEC JS-001 Class 2 exceeds 2 kV
  - CDM (JESD22-C101E)
- Specified from -40°C to +85°C

## **3** Applications

- Smartphone
- Tablet
- Other portable electronic devices



High-voltage back-to-back OVP switch

# 4 Ordering information

Table 1. Ordering information									
Type number	Topside	Package							
	marking	Name	Description	Version					
NX30P0121UK	N21	WLCSP12	wafer level chip scale package; 12 bumps; 0.4 mm pitch; 1.65 mm x 1.25 mm x 0.525 mm body (backside coating included)	SOT1390-8					

## 4.1 Ordering options

#### Table 2. Ordering options

Type number	Orderable part number	Package	<b>J</b>	Minimum order quantity	Temperature
NX30P0121UK	NX30P0121UKZ	WLCSP12	REEL 7" Q1 DP CHIPS	4000	T <sub>amb</sub> = -40 °C to +85 °C

# 5 Functional diagram



# NX30P0121UK

#### High-voltage back-to-back OVP switch



# 6 **Pinning information**

## 6.1 Pinning



### 6.2 Pin description

Table 3.							
Pin description							
Symbol	Pin	Туре	Description				
VIN	A2, B2, C2, D2	Р	Input power pin. Connect bypass capacitor 1uF to GND				

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Pin description								
Symbol	Pin	Туре	Description					
VOUT	A3, B3, C3, D3	Р	Output Power pin, Connect bypass capacitor 1uF to GND					
EN	B1	DIN	Enable pin. Drive HIGH to enable device.					
ISNS	C1	AO	1,053:1 current mirror of input current from VIN to VOUT. Must connect a resistor on ISNS pin to GND to monitor the input current.					
OVLO	A1	AIN	Adjustable OVLO threshold with external Resistor divider					
GND	D1	Р	Ground					

# 7 Functional description

#### Table 4. Function table

EN	VIN	VOUT	Switch	ISNS	Operation
L	Х	Х	OFF	Hi-Z	Shutdown mode
Н	< VIN <sub>UVLO</sub>	Х	OFF	Hi-Z	Standby mode, Undervoltage lockout
Н	Х	> VOUT <sub>OVLO</sub>	OFF	Hi-Z	Standby mode, Overvoltage lockout
Н	> VIN <sub>UVLO</sub>	< VOUT <sub>OVLO</sub>	ON	ON	Switch ON mode

#### 7.1 EN pin

When EN is driven LOW, the device enters shutdown mode regardless of VIN and VOUT voltage. All internal circuitries are off to minimize current consumption and OVP switch is OFF. When EN is driven HIGH, the OVP switch is ready to turn on depending on VIN and VOUT condition. if VIN is above VIN<sub>UVLO</sub> and VOUT is lower than VOUT<sub>OVLO</sub>, the device soft starts after VIN debounce timer is expired, to reduce in-rush current. There is an internal 1M $\Omega$  pull-down resistor in EN pin, which secure EN status in case EN pin is float. This pin has +29V tolerance.

### 7.2 Undervoltage Lockout (UVLO)

When EN is driven HIGH and VIN < VIN<sub>UVLO</sub>, the UVLO circuit disables the power MOSFET. Once VIN exceeds  $VIN_{UVLO}$  and no other protection circuit is active, the channel MOSFET state is controlled by the EN pin.

### 7.3 Overvoltage Lockout (OVLO)

When EN is driven HIGH and VOUT is above VOUT<sub>OVLO</sub>, the OVLO circuit disables the power MOSFET within  $t_{dis(OVP)}$ . Once VOUT drops below VOUT<sub>OVLO</sub> and no other protection circuit is active, the power MOSFET resumes operation.

OVLO pin is used to adjust the overvoltage protection threshold. The default overvoltage threshold is 14.5V when OVLO pin is shorted to GND. Connecting a resistor divider to the OVLO pin (see Figure 4) adjusts the overvoltage threshold from 4V to 20V using below equation.

 $VOUT_{OVLO} = Vth(OVLO) X (R1 + R2)/(R2)$ 

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Where Vth(OVLO) = 1.227V

R1 is recommended to use  $1M\Omega$  resistance.

When the voltage on OVLO pin is below 0.1V, the device defaults to the 14.5V OVP threshold.



### 7.4 Over-temperature protection

When EN is HIGH and the device temperature exceeds 145°C the Over-Temperature Protection (OTP) circuit disables the power MOSFET. Once the device temperature decreases below 115 °C and no other protection circuit is active, the state of the OVP MOSFET is controlled by the EN pin again.

### 7.5 ISNS pin

The ISNS pin is current source output having 1,053:1 ratio with input current from VIN to VOUT. It requires a resistor from ISNS to GND to monitor input current. When device is disabled, its output is high impedance. The ISNS voltage is determined by below equation.  $R_{ISNS}$  is recommended to be +/-1% tolerant.

 $V_{ISNS}$  = (  $I_{IN} \times R_{ISNS}$  ) / 1,053

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## 7.6 Timing diagram



# 8 Application diagram

The NX30P0121UK is typically used to add wireless charger path in single input switching mode charger application. If wireless charger is used, then NX30P0121UK bridge wireless charger output to the switching mode charger, protecting wireless charger from up to 29V which could be from VBUS.

For best performance, it is recommended to keep input and output traces short and wide, and capacitors as close to the device as possible. Regarding thermal performance, it is recommended to increase the PCB area around VIN and VOUT pins.

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# 9 Limiting values

Table 5.	Limiting	values	(absolute	maximum	ratings)
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Symbol	Parameter	Conditions	Min	Мах	Unit
VI	Input voltage (with respect	VIN	-0.5	+29	V
	to GND)	VOUT	-0.5	+29	V
		OVLO	-0.5	VOUT	V
		EN	-0.5	+29	V
		ISNS	-0.5	+6	V
I <sub>IK</sub>	Input clamping current	EN; VI < -0.5 V	-50	-	mA
I <sub>SK</sub>	Switch clamping current	VIN, VOUT; VI < -0.5 V	-50	-	mA
I <sub>SW</sub>	Continuous switch current	T <sub>amb</sub> = 85 °C	-	+3.0	А
		T <sub>amb</sub> = 105 °C	-	+3.0	А
	Peak switch current	130µs pulse, 5% duty cycle at 85 °C	-	+10	А
T <sub>stg</sub>	Storage temperature		-65	+150	°C
P <sub>tot</sub>	Total power dissipation	T <sub>amb</sub> = 25 °C	-	1.45	W

# **10** Recommended operating conditions

Table 6. R	Recommended operating conditions				
Symbol	Parameter	Conditions	Min	Мах	Unit
VI	input voltage (with respect to GND)	VIN	2.5	20	V
		VOUT	2.5	20	V
		EN	0	20	V

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Symbol	Parameter	Conditions	Min	Max	Unit
		ISNS	0	+6	V
T <sub>j(max)</sub>	Maximum junction temperature		-40	+125	°C
T <sub>amb</sub>	Ambient temperature		-40	+85	°C

# **11** Thermal characteristics

#### Table 7. Thermal characteristics

Symbol	Parameter	Conditions		Тур	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient		[1] [2]	70.8	°C/W

Determined in accordance to JEDEC JESD51-2A natural convection environment. Thermal resistance data in this report is solely for a thermal [1] performance comparison of one package to another in a standardized specified environment. It is not meant to predict the performance of a package in an application-specific environment Thermal test board meets JEDEC specification for this package (JESD51-9).

[2]

# **12 Electrical characteristics**

## 12.1 Static characteristics

#### Table 8. Static characteristics

At recommended input voltages and  $T_{amb} = -40^{\circ}$ C to +85°C; voltages are referenced to GND (ground = 0 V); unless otherwise specified.

Symbol	Parameter	Conditions	Ta	<sub>mb</sub> = 25	°C		Unit	
			Min	Тур	Мах	Min	Мах	
1	V <sub>IN</sub> quiescent	EN = 1.8V, V <sub>IN</sub> = 5V, IO = 0A	-	110	-	-	170	μA
Iq	current	EN = 1.8V, V <sub>IN</sub> = 14V, IO = 0A	-	140	-	-	220	μA
1.	V <sub>IN</sub> shutdown Ieakage current	EN = 0V, V <sub>IN</sub> = 5.0V; V <sub>OUT</sub> = 0V	-	5	-	2	10	μΑ
I <sub>SHDN</sub>	V <sub>OUT</sub> shutdown Leakage current	EN = 0V, V <sub>OUT</sub> = 5.0 V, V <sub>IN</sub> = 0 V	-	1	3	-	5	μA
I <sub>OVLO</sub>	OVLO input leakage Current	V <sub>OVLO</sub> =V <sub>th(OVLO)</sub>	-	0.5	-	-	25	nA
R <sub>ON</sub>	ON resistance	V <sub>IN</sub> = 5.0 V	-	54	66	-	79	mΩ
NON	ONTESISIANCE	V <sub>IN</sub> = 14 V	-	54	66	-	Max         170         220         10         5         25         79         2.6         140	mΩ
V <sub>INUVLO</sub>	V <sub>IN</sub> UVLO voltage	V <sub>IN</sub> Rising; EN = 1.8V	2.2	2.37	2.55	2.1	2.6	V
V <sub>INhys(UVLO)</sub>	V <sub>IN</sub> UVLO hysteresis voltage	V <sub>IN</sub> Falling	-	110	-	-	140	mV
V <sub>OUTOVLO</sub>	Default overvoltage lockout voltage	V <sub>OUT</sub> Rising; EN = 1.8V OVLO short to GND	-	14.5	-	13.5	15.3	V

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Symbol	Parameter	Conditions	Ta	<sub>mb</sub> = 25	°C	T <sub>amb</sub> = to +8	Unit	
			Min	Тур	Мах	Min	Мах	
		V <sub>OUT</sub> Falling; EN = 1.8V OVLO short to GND	-	14.2	-	13.2	15.0	V
V <sub>th(OVLO)</sub>	external OVLO set threshold voltage	V <sub>OUT</sub> = 2.5 V to 20 V; EN = 1.8V	1.163	1.227	1.288	1.16	1.3	V
V <sub>IH</sub>	HIGH-level input voltage	EN pin; V <sub>IN</sub> = 2.5 V to 20 V	1.2	-	-	1.2	-	V
V <sub>IL</sub>	LOW-level input voltage	EN pin; V <sub>IN</sub> = 2.5 V to 20 V	-	-	0.4	-	0.4	V
R <sub>pd</sub>	pull-down resistance	EN	-	1	-	0.7	1.4	MΩ
CI	input capacitance	EN pin; V <sub>IN</sub> = 5V	-	2	-	-	-	pF
к	Current sensing ratio	I <sub>IN</sub> / I <sub>ISNS</sub> , I <sub>IN</sub> = 1A, V <sub>IN</sub> = 5V, EN =1.8V		1050		1010	1090	A/A
V <sub>ISNS</sub>	ISNS voltage	$I_{\rm IN}$ = 2A, $R_{\rm ISNS}$ = 4000, $V_{\rm IN}$ = 5V, $V_{\rm IN}$ > 3.0V		0.762				V
V <sub>ISNS</sub>	ISNS voltage	$I_{\rm IN}$ = 1A, $R_{\rm ISNS}$ = 806Ω, $V_{\rm IN}$ = 5V, $V_{\rm IN}$ > 3.0V		0.767				V
V <sub>ISNS</sub>	ISNS voltage	$I_{IN}$ = 0.5A, $R_{ISNS}$ = 806Ω, $V_{IN}$ = 5V, $V_{IN}$ > 3.0V		0.384				V
T <sub>th(OTP)</sub>	Over temperature shutdown threshold	EN = 1.8V	-	145	-	-	-	°C
T <sub>th(OTP)Hys</sub>	Over temperature shutdown threshold hysteresis	EN = 1.8V	-	30	-	-	-	°C

## 12.2 Dynamic characteristics

#### Table 9. Dynamic characteristics

Symbol	Parameter	Conditions	T <sub>amb</sub> = 25 °C			T <sub>amb</sub> = -40 °C to +85 °C		Unit
			Min	Тур	Мах	Min	Мах	
t <sub>en</sub>	Enable Time		3.5	5.5	8.0	3.0	11.0	ms
	V <sub>OUT</sub> rise time	$V_{OUT}$ from 10% to 90% of $V_{IN}$ ; $C_{OUT}$ = 10µF; $R_{OUT}$ = 100Ω						
t <sub>TLH</sub>		V <sub>IN</sub> = 5 V	-	1.8	-	-	-	ms
		V <sub>IN</sub> =14 V	-	3.0	-	-	-	ms
t <sub>dis(OVP)</sub>	OVP turn off time	From V <sub>OUT</sub> > VOUT <sub>OVLO</sub> to V <sub>VIN</sub> = 80% of V <sub>OUT</sub> ; Rload_V <sub>IN</sub> = 100 $\Omega$ ,;C <sub>IN</sub> = 0uF; V <sub>IN</sub> = 12V; OVLO pin short to GND	-	70	-	-	-	ns
t <sub>on</sub>	turn-on time	EN to $V_{OUT}$ = 90% of $V_{IN}$						

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### High-voltage back-to-back OVP switch

Symbol	Parameter	Conditions	T <sub>amb</sub> = 25 °C			T <sub>amb</sub> = -40 °C to +85 °C		Unit
			Min	Тур	Мах	Min	Мах	
		V <sub>IN</sub> = 5.0 V	-	7.5	-	5.0	10.0	ms
		V <sub>IN</sub> = 14.0 V	-	9.0	-	-	-	ms
t <sub>off</sub>	turn-off time	EN to $V_{OUT}$ = 10% $V_{IN}$						
		$V_{IN}$ = 5.0 V; $C_{OUT}$ = 10µF; $R_{OUT}$ = 100 $\Omega$	-	2.6	4.0	-	4.0	ms
		$V_{IN}$ = 14 V; $C_{OUT}$ = 10µF; $R_{OUT}$ = 100Ω	-	2.6	-	-	-	ms

## 12.3 Graphs





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# 13 Package outline



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ΝΟΊ	TES:
1.	ALL DIMENSIONS IN MILLIMETERS.
2.	DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
3.	PIN A1 FEATURE SHAPE, SIZE AND LOCATION MAY VARY.
4.	MAXIMUM SOLDER BALL DIAMETER MEASURED PARALLEL TO DATUM C.
<u>/5.</u>	DATUM C, THE SEATING PLANE, IS DETERMINED BY THE SPHERICAL CROWNS OF THE SOLDER BALLS.
6.	THIS PACKAGE HAS A BACK SIDE COATING THICKNESS OF 0.025.
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	MECHANICAL OUTLINE STANDARD: DRAWING NUMBER: REVISION:
	PRINT VERSION NOT TO SCALE NON JEDEC SOT1390-8 0

Figure 15. Package outline SOT1390-8 (WLCSP12) (2 of 2)

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## 14 Soldering



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# **15 Revision history**

Table 10.         Revision history				
Document ID	Release date	Data sheet status	Change notice	Supersedes
NX30P0121 v.1.0	20190619	Product data sheet	-	-

# **16 Legal information**

## 16.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] [3] The term 'short data sheet' is explained in section "Definitions".

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Date of release: 19 June 2019 Document identifier: NX30P0121